

V_{DSS}	200V
$R_{DS(on)}$ (Max.)	180mΩ
I_D	16A
P_D	40W

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating ; RoHS compliant
- 6) 100% Avalanche tested

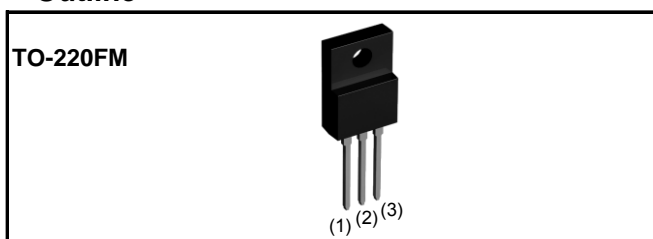
●Application

Switching Power Supply
 Automotive Motor Drive
 Automotive Solenoid Drive

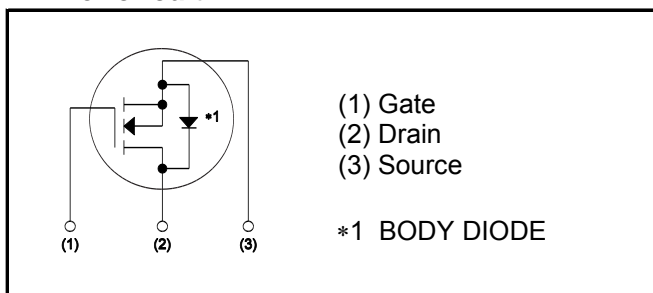
●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	200	V
Continuous drain current	$T_c = 25^\circ\text{C}$	I_D^{*1}	±16	A
	$T_c = 100^\circ\text{C}$	I_D^{*1}	±8.7	A
Pulsed drain current		$I_{D,pulse}^{*2}$	±64	A
Gate - Source voltage		V_{GSS}	±30	V
Avalanche energy, single pulse		E_{AS}^{*3}	20.7	mJ
Avalanche current		I_{AS}^{*3}	8.0	A
Power dissipation	$T_c = 25^\circ\text{C}$	P_D	40	W
	$T_a = 25^\circ\text{C}$	P_D	2.23	W
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	-55 to +150	°C

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Bulk
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	RCX160N20

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	-	3.125	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	56	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	200	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V$ $T_j = 25^\circ\text{C}$	-	-	10	μA
		$V_{DS} = 200V, V_{GS} = 0V$ $T_j = 125^\circ\text{C}$	-	-	100	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	3.25	-	5.25	V
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	$V_{GS} = 10V, I_D = 8.0A$	-	135	180	$m\Omega$
		$V_{GS} = 10V, I_D = 8.0A$ $T_j = 125^\circ\text{C}$	-	295	410	
Forward transfer admittance	g_{fs}	$V_{DS} = 10V, I_D = 8.0A$	4.0	8.0	-	S

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C _{iss}	V _{GS} = 0V	-	1370	-	pF
Output capacitance	C _{oss}	V _{DS} = 25V	-	95	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	50	-	
Turn - on delay time	t _{d(on)} ^{*4}	V _{DD} ≈ 100V, V _{GS} = 10V	-	27	-	ns
Rise time	t _r ^{*4}	I _D = 8.0A	-	47	-	
Turn - off delay time	t _{d(off)} ^{*4}	R _L = 12.5Ω	-	42	-	
Fall time	t _f ^{*4}	R _G = 10Ω	-	17	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*4}	V _{DD} ≈ 100V	-	26	-	nC
Gate - Source charge	Q _{gs} ^{*4}	I _D = 16A	-	10	-	
Gate - Drain charge	Q _{gd} ^{*4}	V _{GS} = 10V	-	11	-	
Gate plateau voltage	V _(plateau)	V _{DD} ≈ 100V, I _D = 16A	-	7.0	-	V

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I _S ^{*1}	T _c = 25°C	-	-	16	A
Pulsed source current	I _{SM} ^{*2}		-	-	64	A
Forward voltage	V _{SD} ^{*4}	V _{GS} = 0V, I _S = 16A	-	-	1.5	V
Reverse recovery time	t _{rr} ^{*4}	I _S = 8.0A	-	85	-	ns
Reverse recovery charge	Q _{rr} ^{*4}	di/dt = 100A/μs	-	300	-	nC

*1 Limited only by maximum temperature allowed.

*2 P_w ≤ 10μs, Duty cycle ≤ 1%

*3 L ≈ 500μH, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C

*4 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

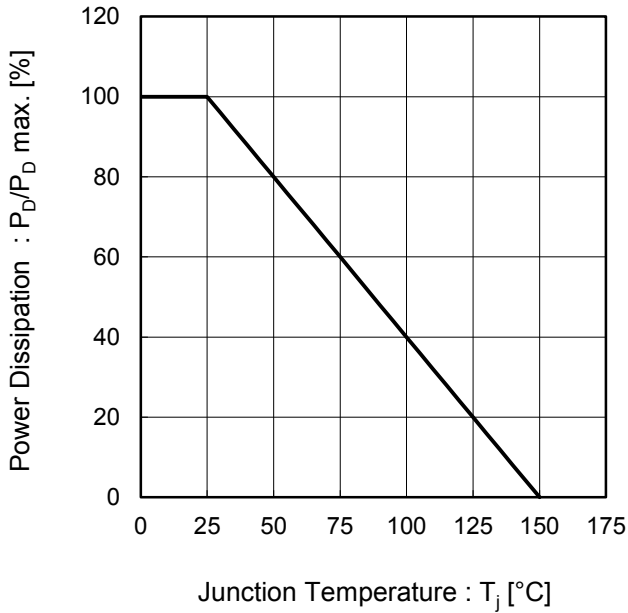


Fig.2 Maximum Safe Operating Area

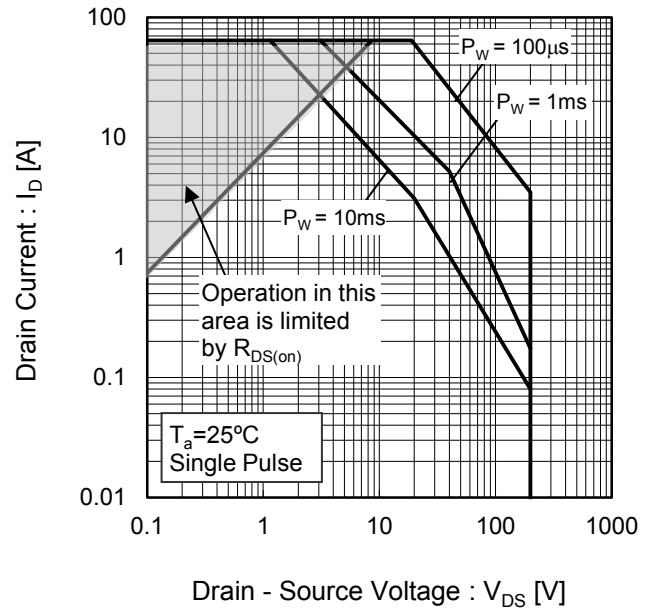
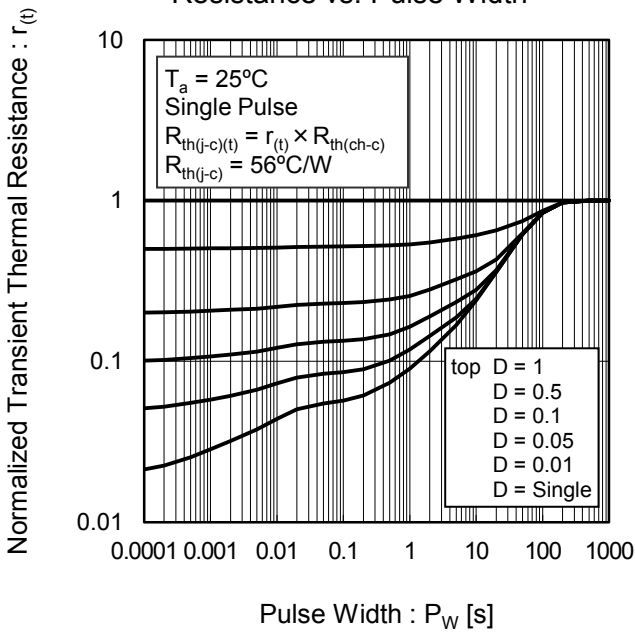


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

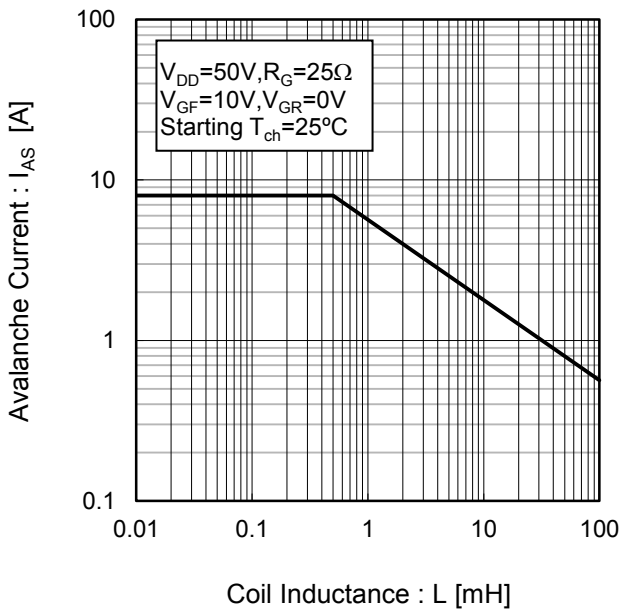


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature

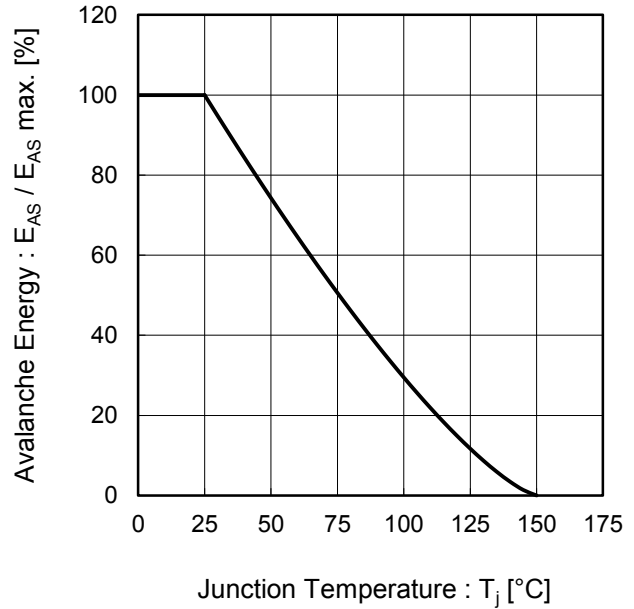


Fig.6 Typical Output Characteristics(I)

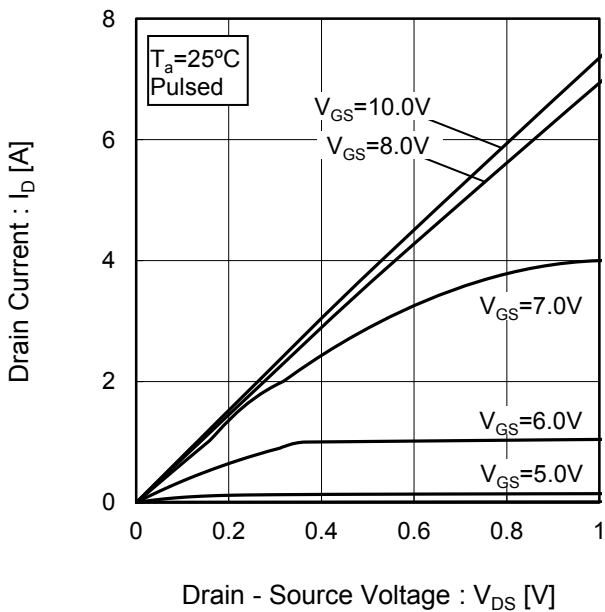
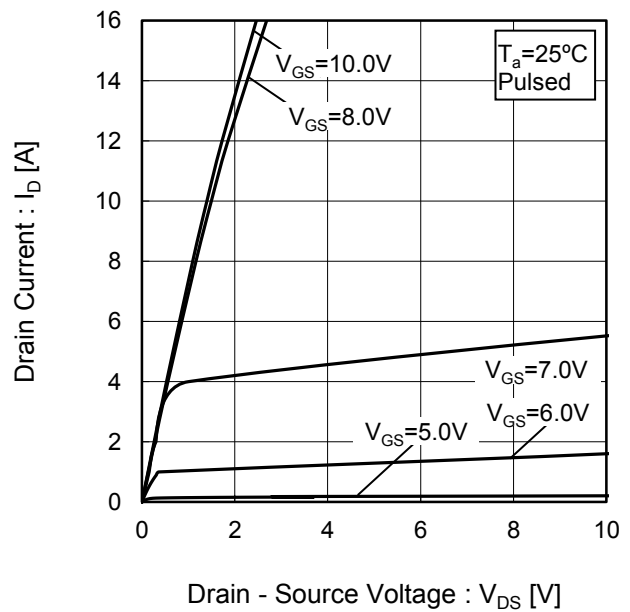


Fig.7 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Breakdown Voltage vs. Junction Temperature

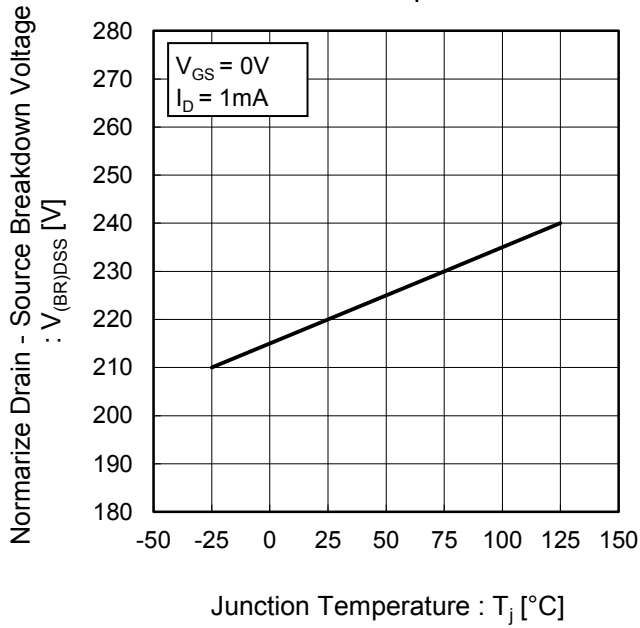


Fig.9 Typical Transfer Characteristics

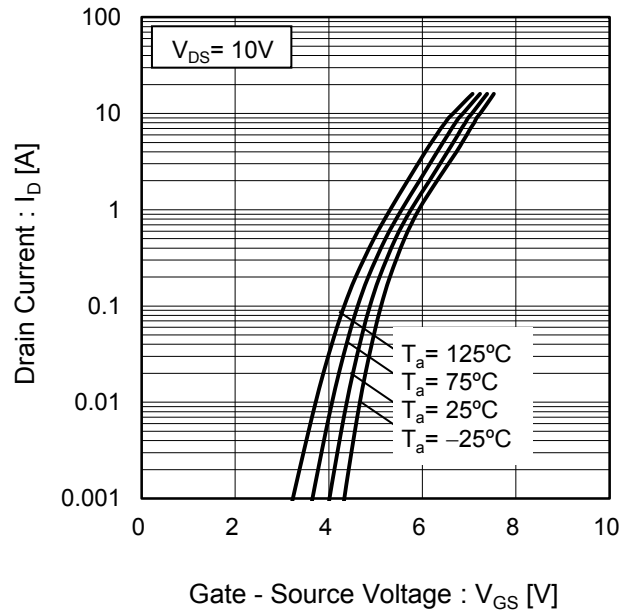


Fig.10 Gate Threshold Voltage vs. Junction Temperature

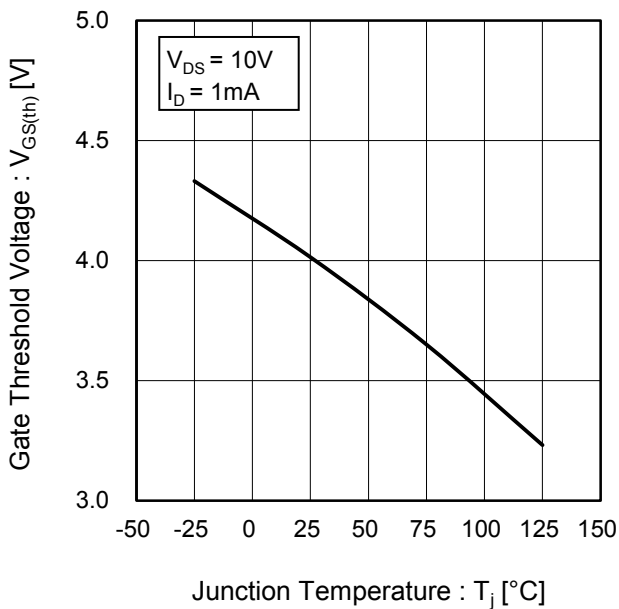
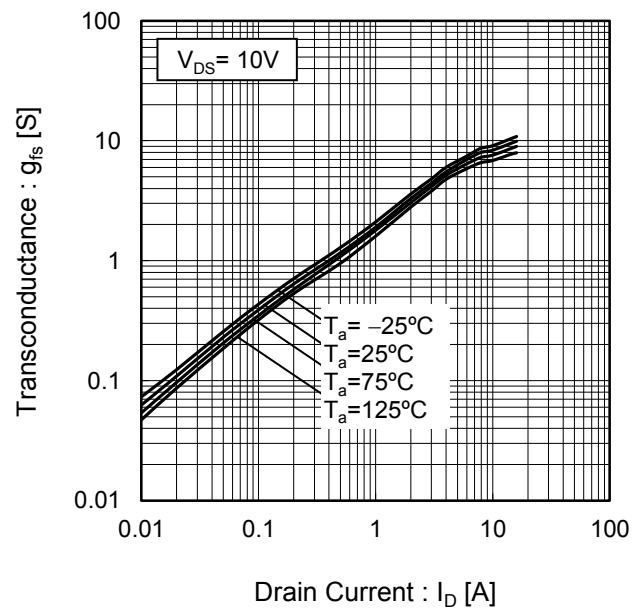


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

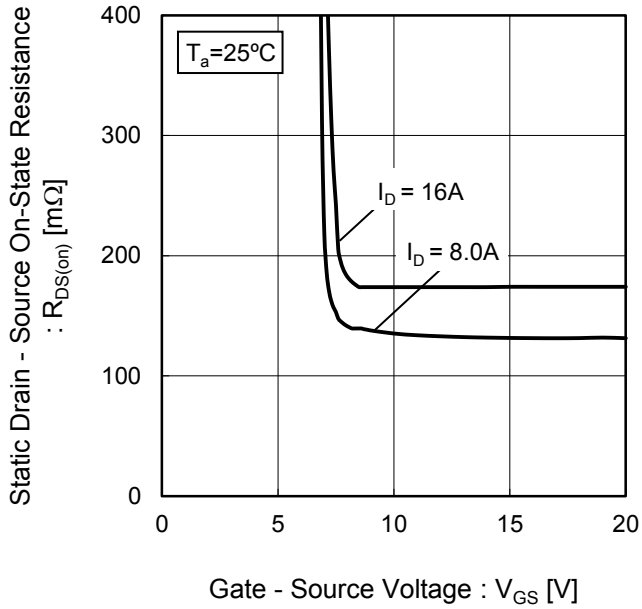


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

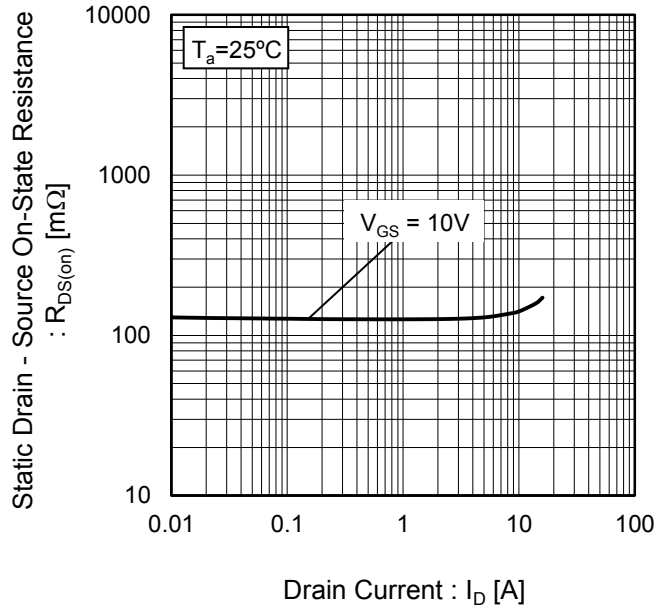
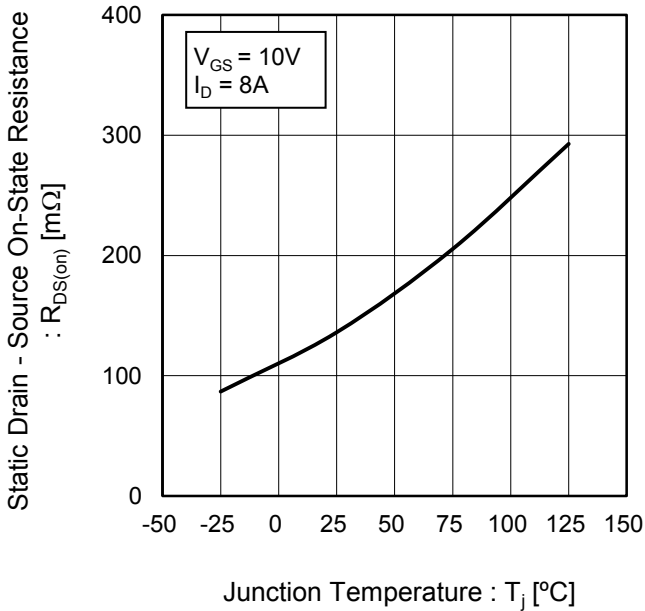


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(I)

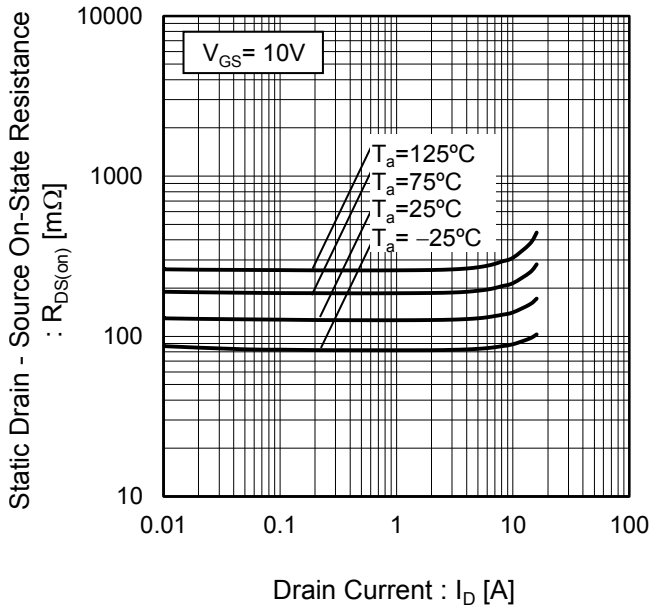
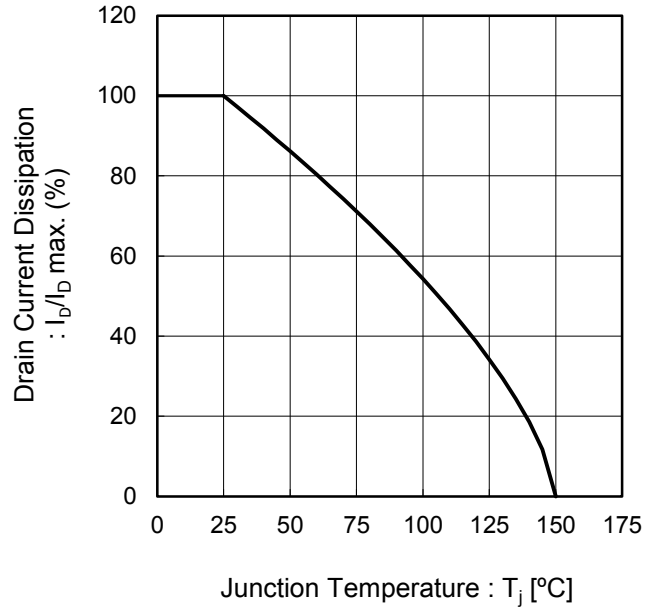


Fig.16 Drain Current Derating Curve



●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

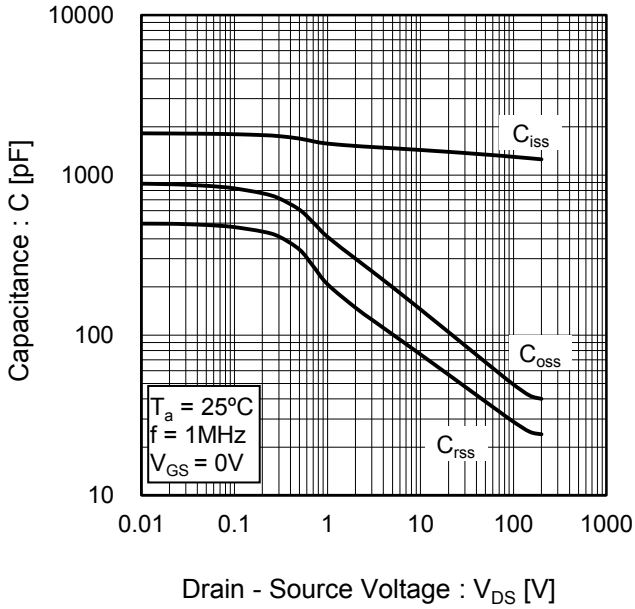


Fig.18 Switching Characteristics

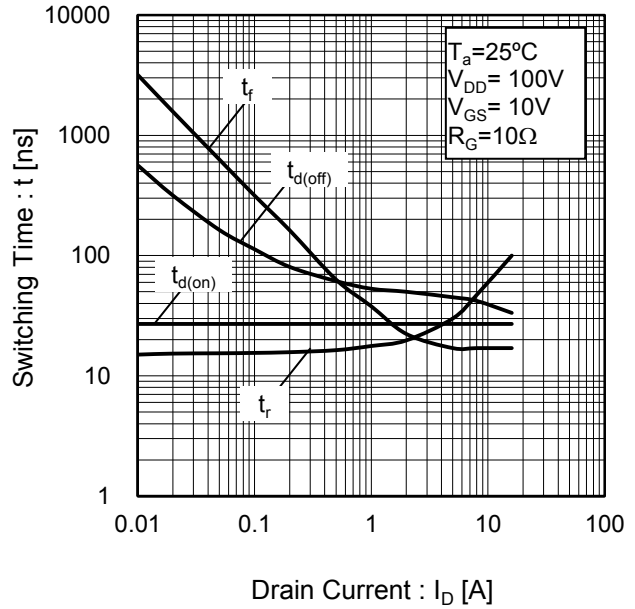
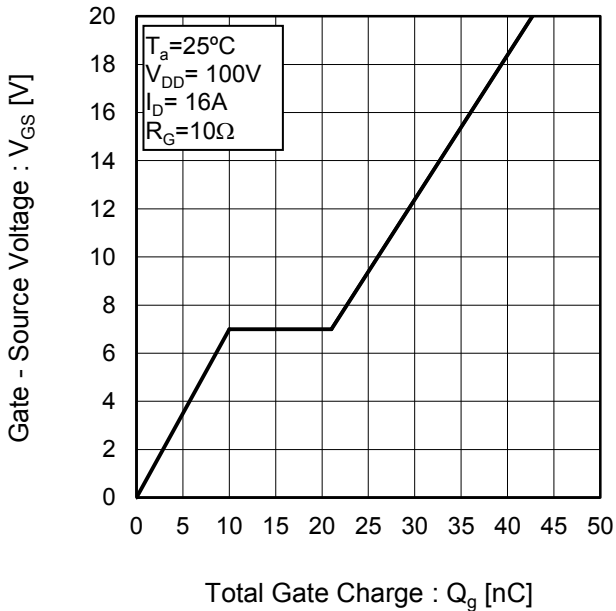


Fig.19 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.20 Source Current vs. Source - Drain Voltage

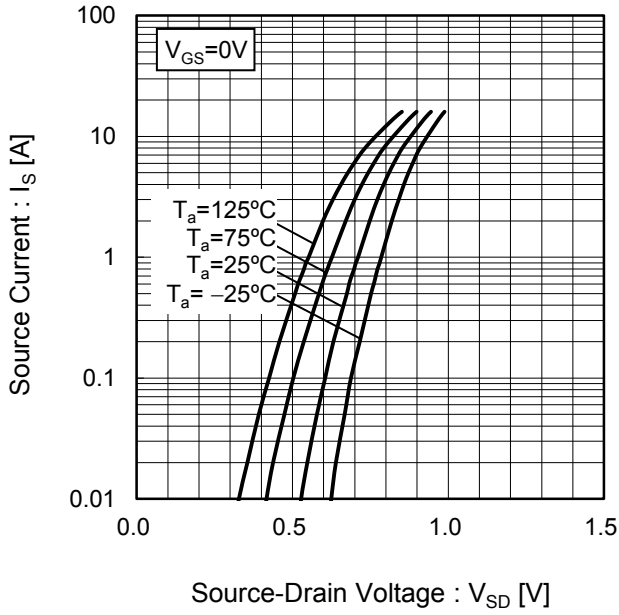
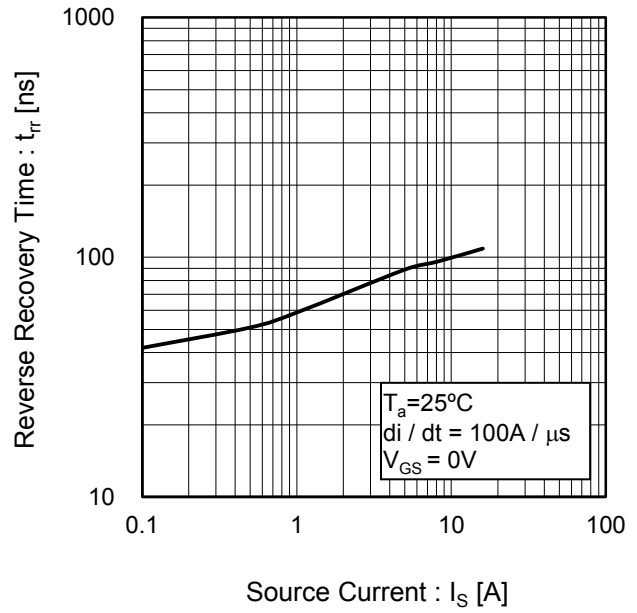


Fig.21 Reverse Recovery Time vs. Source Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

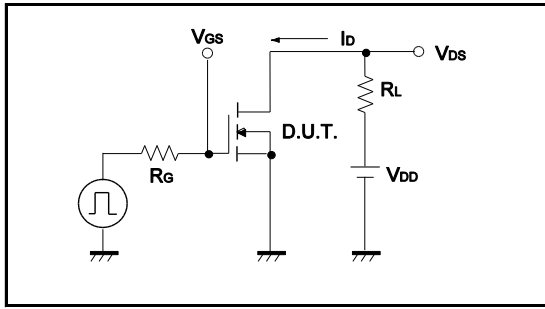


Fig.1-2 Switching Waveforms

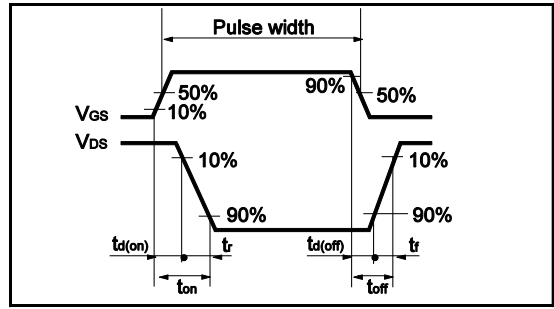


Fig.2-1 Gate Charge Measurement Circuit

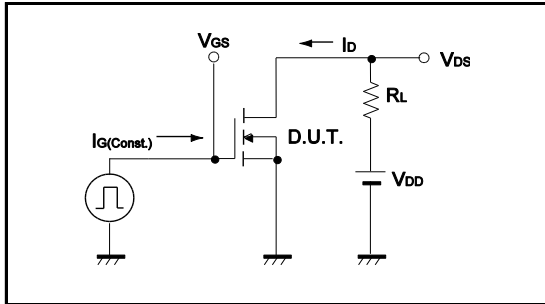


Fig.2-2 Gate Charge Waveform

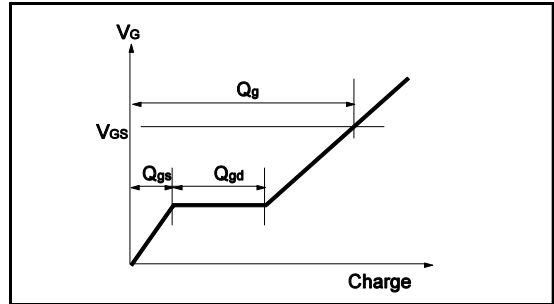


Fig.3-1 Avalanche Measurement Circuit

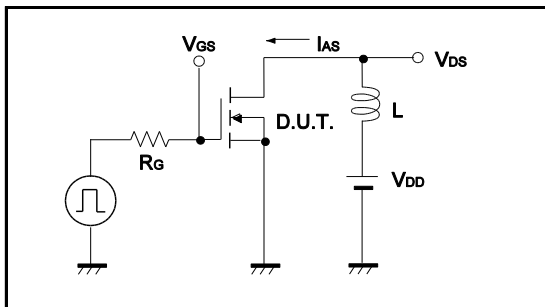
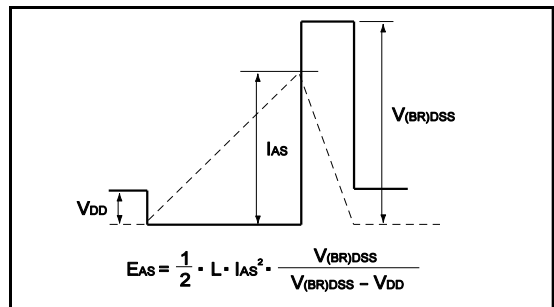
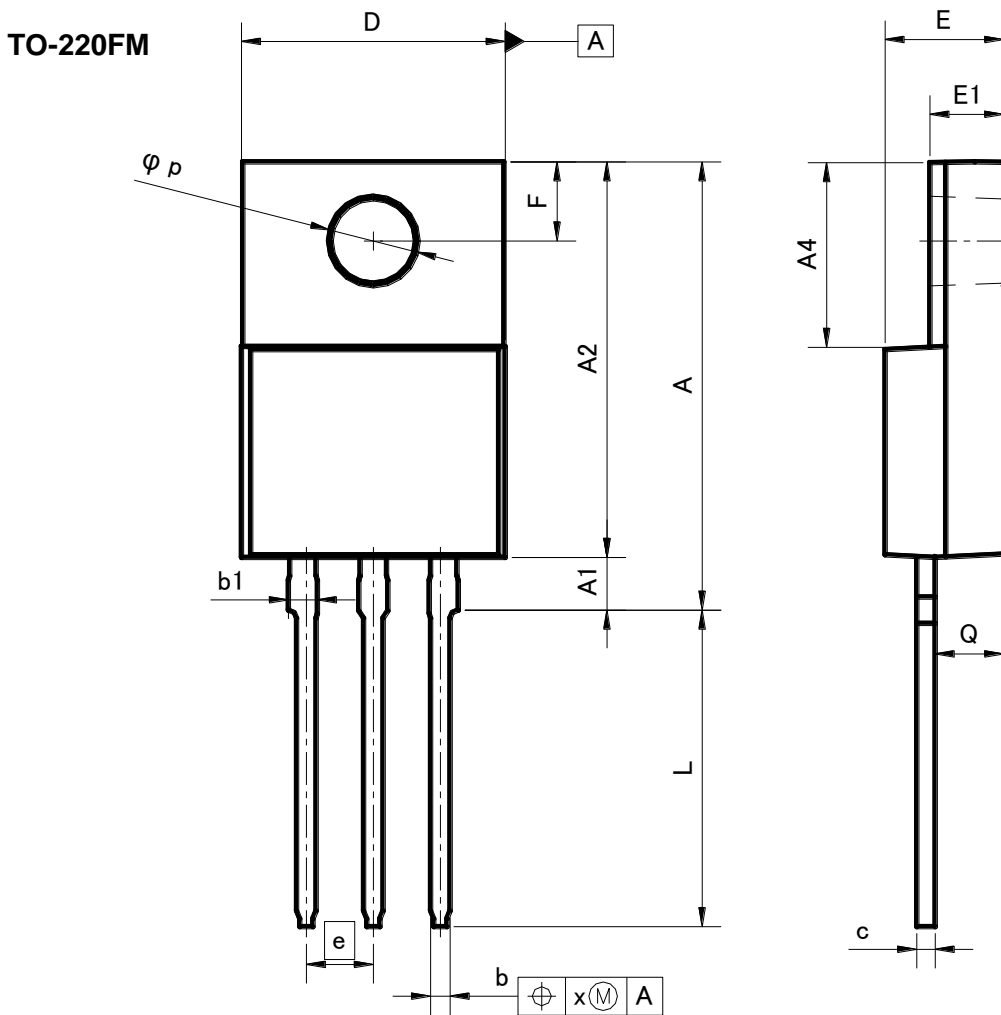


Fig.3-2 Avalanche Waveform



●Dimensions (Unit : mm)



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
c	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
E	4.40	4.80	0.173	0.189
e	2.54		0.10	
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
p	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
x	-	0.381	-	0.015

Dimension in mm/inches

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